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Sheet 1 of 1

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY. DOCKET NO. MI22-2263		10/612,836 SERIAL NO. Filed Herewith	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)					APPLICANT Ronald A. Weimer et al.			
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U.S. PATENT DOCUMENTS								
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W.F.	AR		Improved Hot-Electron Reliability in High-Performance, Multilevel-Metal CMOS Using Deuterated Barrier-Nitride Processing; W.F. Clark et al; IEEE Electron Device Letters, Vol. 20, No. 10, pps. 501-503, October 1999.					
W.F.	AS		Realization of High Performance Dual Gate DRAMs without Boron Penetration by Application of Tetrachlorosilane Silicon Nitride Films; Masayuki Tanaka et al.; 2001 Symposium VLSI Technology Digest of Technical Papers, pps. 123-124					
EXAMINER <i>Stephen W. Smart</i>				DATE CONSIDERED <i>September 2, 2004</i>				
<small>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small>								